

TOSHIBA
MICROWAVE SEMICONDUCTOR
TECHNICAL DATA

MICROWAVE POWER GaAs FET
TIM5359-35SL

FEATURES

n **LOW INTERMODULATION DISTORTION**

IM3=-45 dBc at Pout= 35.0dBm

Single Carrier Level

n **HIGH POWER**

P1dB=45.5dBm at 5.3GHz to 5.9GHz

n **HIGH GAIN**

G1dB=8.5dB at 5.3GHz to 5.9GHz

n **BROADBAND INTERNALLY MATCHED**

n **HERMETICALLY SEALED PACKAGE**

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V f = 5.3 to 5.9GHz	dBm	45.0	45.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5	—
Drain Current	IDS1		A	—	8.0	9.0
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	38	—
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po=35.0dBm	dBc	-42	-45	—
Drain Current	IDS2	(Single Carrier Level)	A	—	8.0	9.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin - P1dB) X Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg) : 28 W (Max.)

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.5A	mS	—	6500	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 140mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	20	26
Gate-Source Breakdown Voltage	VGSO	IGS= -420mA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	1.0	1.3

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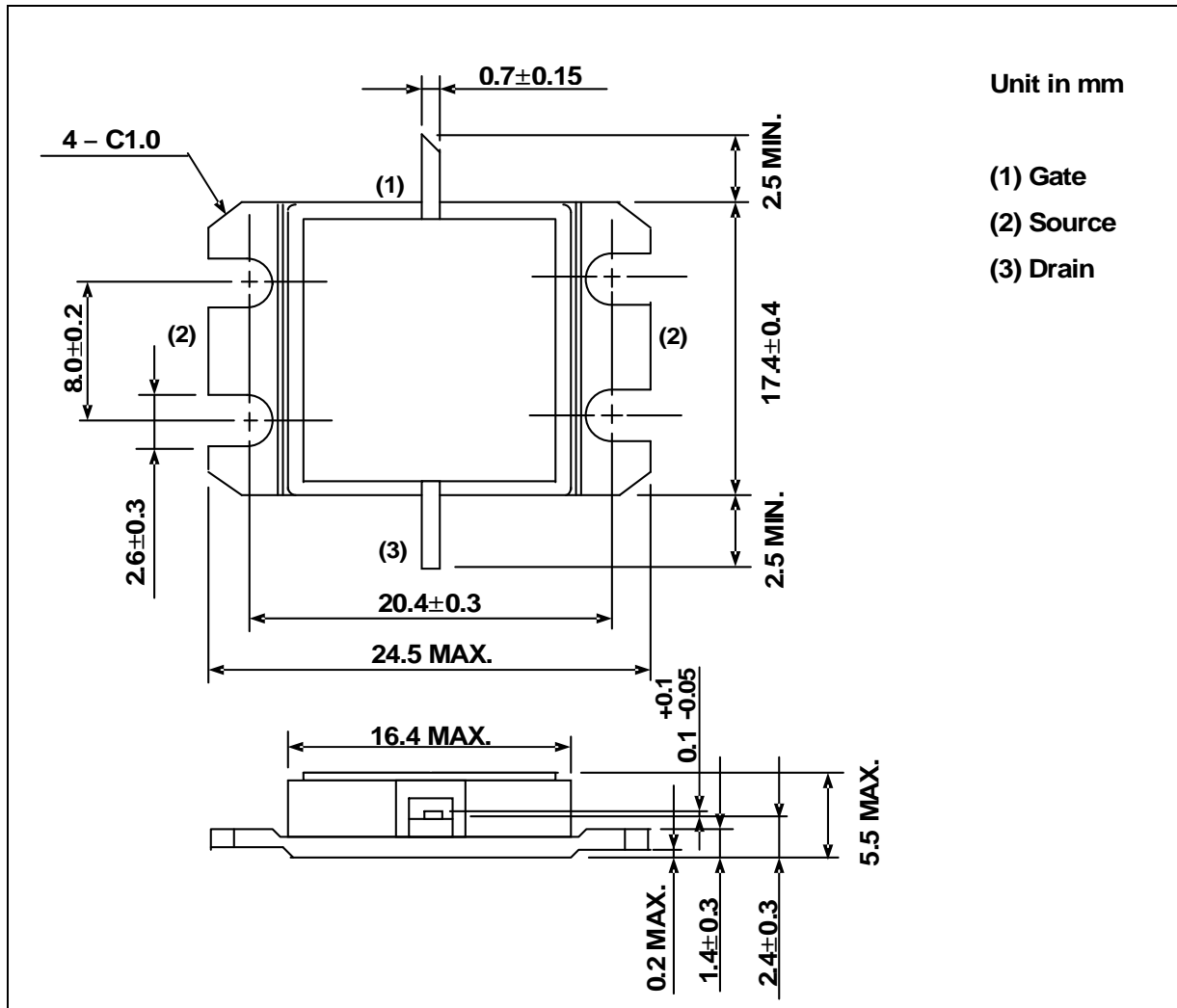
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	20
Total Power Dissipation (T _c = 25 °C)	PT	W	115.4
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)

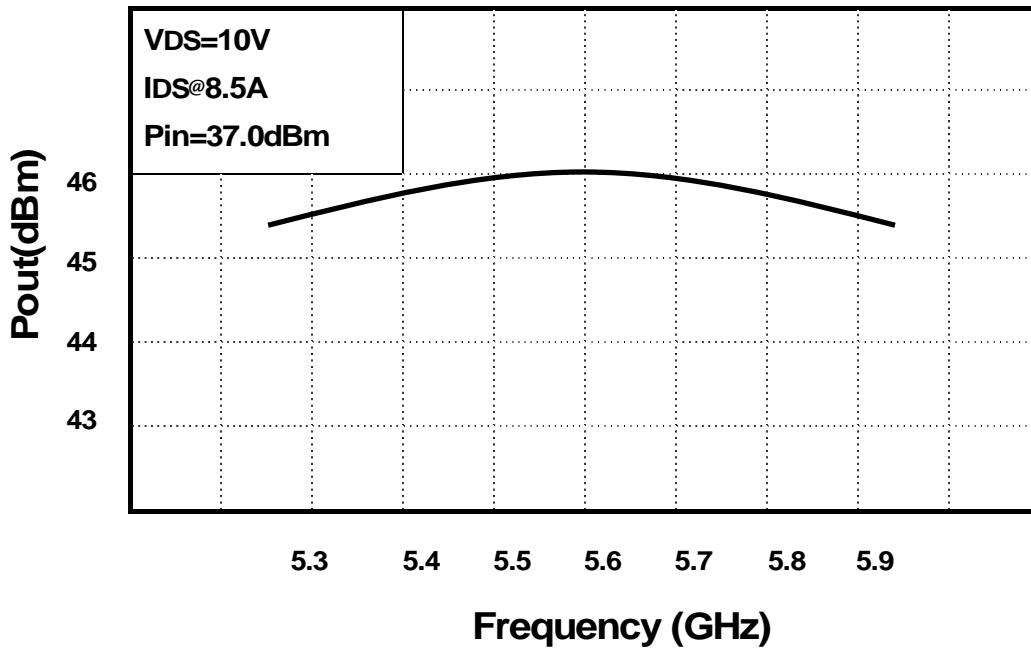


HANDLING PRECAUTIONS FOR PACKAGE MODEL

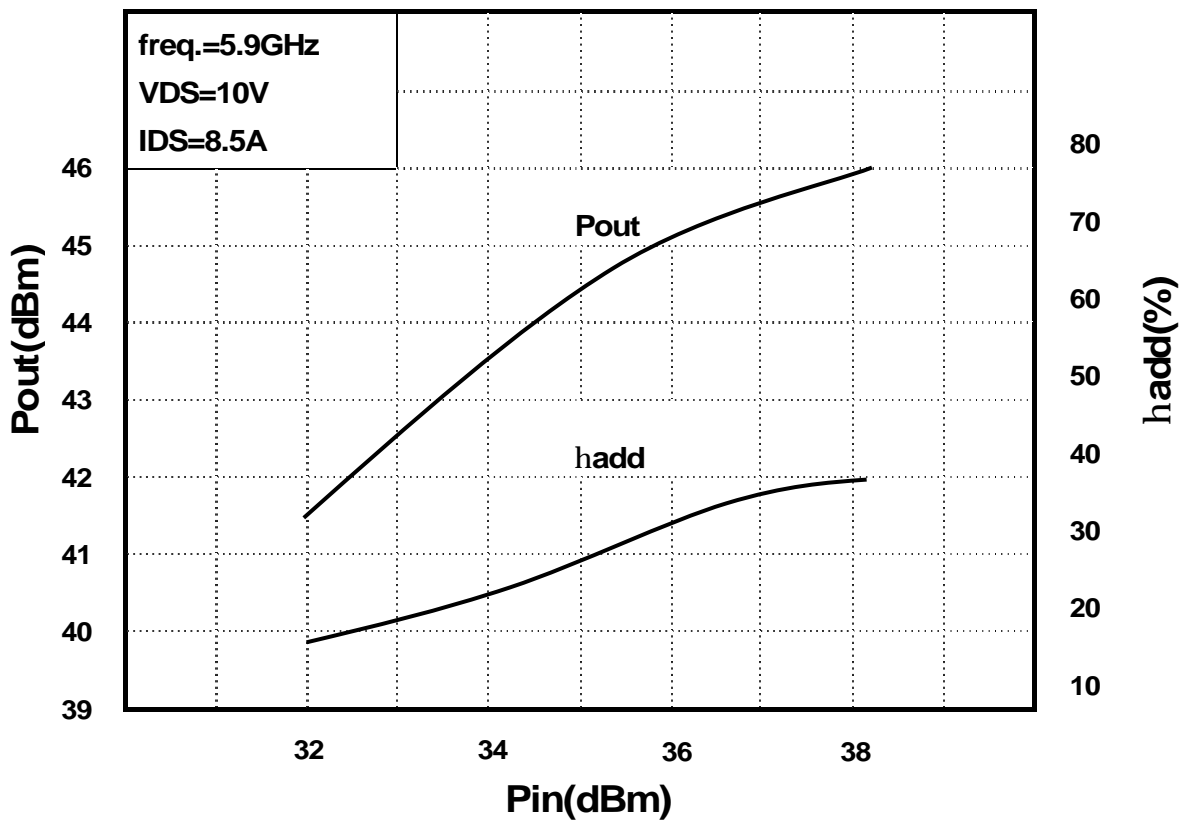
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCES

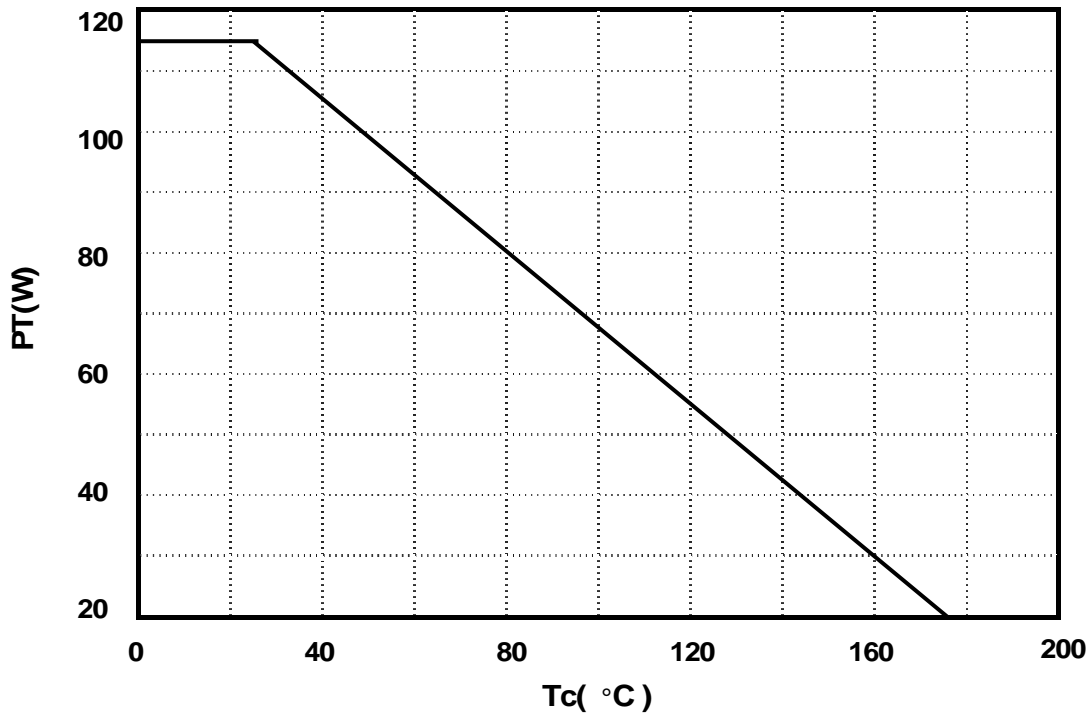
Output Power (Pout) vs. Frequency



Output Power(Pout) vs. Input Power(Pin)



Power Dissipation(PT) vs. Case Temperature(Tc)



IM3 vs. Power Characteristics

